RENESAS

HD74LV2G74A

Single D-type Flip Flops with Preset and Clear

REJ03D0097–0500 (Previous: ADE-205-346D) Rev.5.00 Apr 07, 2006

Description

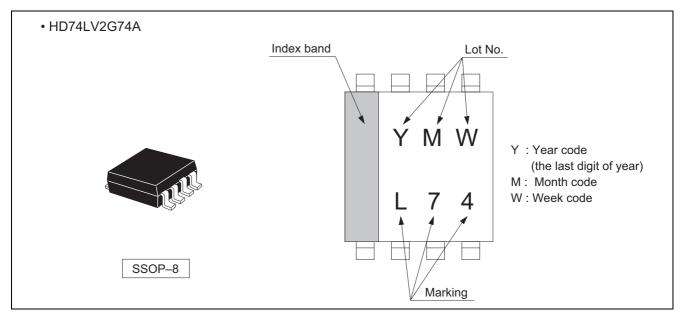
The HD74LV2G74A has independent data, preset, clear, and clock inputs Q and \overline{Q} outputs in an 8 pin package. The input data is transferred to the output at the rising edge of clock pulse CLK. Low voltage and high-speed operation is suitable for the battery powered products (e.g., notebook computers), and the low power consumption extends the battery life.

Features

- The basic gate function is lined up as Renesas uni logic series.
- Supplied on emboss taping for high-speed automatic mounting.
- Electrical characteristics equivalent to the HD74LV74A Supply voltage range : 1.65 to 5.5 V Operating temperature range : -40 to +85°C
- All inputs V_{IH} (Max.) = 5.5 V (@V_{CC} = 0 V to 5.5 V) All outputs V_0 (Max.) = 5.5 V (@V_{CC} = 0 V)
- Output current $\pm 6 \text{ mA}$ (@V_{CC} = 3.0 V to 3.6 V), $\pm 12 \text{ mA}$ (@V_{CC} = 4.5 V to 5.5 V)
- All the logical input has hysteresis voltage for the slow transition.
- Ordering Information

Part Name	Package Type	Package Code (Previous code)	Package Abbreviation	Taping Abbreviation (Quantity)
HD74LV2G74AUSE	SSOP-8 pin	PVSP0008KA-A (TTP-8DBV)	US	E (3,000 pcs / Reel)

Outline and Article Indication





Function Table

	Inp	Outputs			
PRE	CLR	CLK	Q	Q	
L	Н	Х	Х	Н	L
Н	L	Х	Х	L	Н
L	L	Х	Х	H *1	H ^{*1}
Н	Н	↑	Н	Н	L
Н	Н	↑ (L	L	Н
Н	Н	\downarrow	Х	Q ₀	\overline{Q}_0

H : High level

L : Low level

X : Immaterial

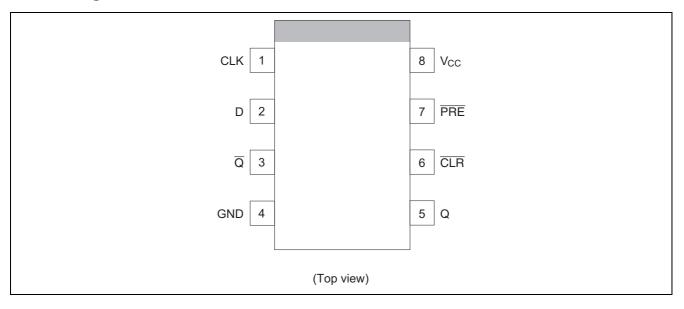
 \uparrow : Low to high transition

 \downarrow : High to low transition

Q₀: The level of Q immediately before the input conditions shown in the above table are determined.

Note : 1. Q and \overline{Q} will remain high as long as preset and clear are low, but Q and \overline{Q} are unpredictable, if preset and clear go high simultaneously.

Pin Arrangement





Absolute Maximum Ratings

ltem	Symbol	Ratings	Unit	Test Conditions
Supply voltage range	V _{CC}	-0.5 to 7.0	V	
Input voltage range ^{*1}	VI	-0.5 to 7.0	V	
Output voltage range ^{*1, 2}	Vo	-0.5 to V _{CC} + 0.5	V	Output : H or L
		-0.5 to 7.0		V _{CC} : OFF
Input clamp current	I _{IK}	-20	mA	V ₁ < 0
Output clamp current	I _{OK}	±50	mA	$V_0 < 0 \text{ or } V_0 > V_{CC}$
Continuous output current	Ι _ο	±25	mA	$V_{O} = 0$ to V_{CC}
Continuous current through V _{CC} or GND	I_{CC} or I_{GND}	±50	mA	
Maximum power dissipation at Ta = 25°C (in still air) ^{*3}	P _T	200	mW	
Storage temperature	Tstg	–65 to 150	°C	

Notes: The absolute maximum ratings are values, which must not individually be exceeded, and furthermore no two of which may be realized at the same time.

1. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

- 2. This value is limited to 5.5 V maximum.
- 3. The maximum package power dissipation was calculated using a junction temperature of 150°C.

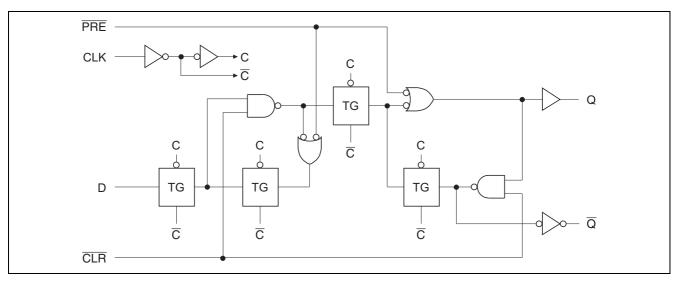
Recommended Operating Conditions

Item	Symbol	Min	Max	Unit	Conditions
Supply voltage range	V _{CC}	1.65	5.5	V	
Input voltage range	VI	0	5.5	V	
Output voltage range	Vo	0	V _{CC}	V	
Output current	I _{OL}	—	1	mA	V _{CC} = 1.65 to 1.95 V
			2		V _{CC} = 2.3 to 2.7 V
			6		V _{CC} = 3.0 to 3.6 V
			12		$V_{CC} = 4.5$ to 5.5 V
	I _{OH}	—	-1		V _{CC} = 1.65 to 1.95 V
			-2		V _{CC} = 2.3 to 2.7 V
			-6		V _{CC} = 3.0 to 3.6 V
			-12		$V_{CC} = 4.5$ to 5.5 V
Input transition rise or fall rate	$\Delta t / \Delta v$	0	300	ns / V	V _{CC} = 1.65 to 1.95 V
		0	200		V _{CC} = 2.3 to 2.7 V
		0	100	1	V _{CC} = 3.0 to 3.6 V
		0	20	1	$V_{CC} = 4.5$ to 5.5 V
Operating free-air temperature	Ta	-40	85	°C	

Note: Unused or floating inputs must be held high or low.



Logic Diagram



Electrical Characteristics

Ta = -40 to $85^{\circ}C$

Item	Symbol	V _{cc} (V) *	Min	Тур	Max	Unit	Test condition
Input voltage	VIH	1.65 to 1.95	V _{CC} ×0.75	_	—	V	
		2.3 to 2.7	V _{CC} ×0.7	_	_		
		3.0 to 3.6	V _{CC} ×0.7	_	_		
		4.5 to 5.5	V _{CC} ×0.7		_		
	VIL	1.65 to 1.95	_	_	V _{CC} ×0.25		
		2.3 to 2.7	_	_	V _{CC} ×0.3		
		3.0 to 3.6	_	_	V _{CC} ×0.3		
		4.5 to 5.5	_	_	V _{CC} ×0.3		
Hysteresis voltage	V _H	1.8	_	0.25	—	V	$V_T^+ - V_T^-$
		2.5	_	0.30	—		
		3.3	_	0.35	—		
		5.0	_	0.45	—		
Output voltage	V _{OH}	Min to Max	V _{cc} -0.1	_	—	V	I _{OH} = -50 μA
		1.65	1.4	_	—		I _{OH} = -1 mA
		2.3	2.0	_	—		I _{OH} = -2 mA
		3.0	2.48	—	—		I _{OH} =6 mA
		4.5	3.8	_	—		I _{OH} = -12 mA
	V _{OL}	Min to Max	_	_	0.1		I _{OL} = 50 μA
		1.65	_	_	0.3		I _{OL} = 1 mA
		2.3	_	_	0.4		I _{OL} = 2 mA
		3.0	_	_	0.44		I _{OL} = 6 mA
		4.5	_	_	0.55		I _{OL} = 12 mA
Input current	I _{IN}	0 to 5.5	_	_	±1	μΑ	$V_{IN} = 5.5 \text{ V or GND}$
Quiescent supply current	I _{CC}	5.5	_	_	10	μA	$V_{IN} = V_{CC}$ or GND,
							I _O = 0
Output leakage current	I _{OFF}	0	—		5	μΑ	V_{IN} or $V_O = 0$ to 5.5 V
Input capacitance	CIN	3.3	—	2.5	—	pF	$V_{IN} = V_{CC} \text{ or } GND$

Note: For conditions shown as Min or Max, use the appropriate values under recommended operating conditions.



Switching Characteristics

 $V_{CC} = 1.8 \pm 0.15 \ V$

Item	Symbol		T _a = 25°C	;	$T_a = -40$	to 85°C	Unit	Test	FROM	то
item	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Maximum clock	f _{max}	30	60	—	20	_	MHz	C∟ = 15 pF		
frequency		20	40	—	15	—		C _L = 50 pF		
Propagation	t _{PLH}		16.3	27.0	1.0	29.0	ns	C _L = 15 pF	PRE/CLR	Q or Q
delay time	t _{PHL}		17.9	29.0	1.0	32.0			CLK	
			21.6	34.0	1.0	36.5		C _L = 50 pF	PRE/CLR	Q or Q
			24.5	39.5	1.0	42.5			CLK	
Setup time	t _{su}	13.0	_	—	14.0	_	ns		D	
		9.0			9.0				PRE or CLR	inactive
Hold time	t _h	0.5			0.5		ns			
Pulse width	t _w	12.0		_	13.0		ns		PRE or CLR	"L"
		12.0	—	_	13.0	—			CLK "H" or "I	"

 $V_{CC}=2.5\pm0.2~V$

ltem	Symbol		T _a = 25°C	;	$T_a = -40$	to 85°C	Unit	Test	FROM	ТО
item	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Maximum clock	f _{max}	50	100	_	40	_	MHz	C∟ = 15 pF		
frequency		30	70	—	25			C∟ = 50 pF		
Propagation	t _{PLH}	—	9.8	14.8	1.0	17.0	ns	C∟ = 15 pF	PRE/CLR	Q or Q
delay time	t _{PHL}		11.1	16.4	1.0	19.0			CLK	
			13.0	17.4	1.0	20.0		C∟ = 50 pF	PRE/CLR	Q or Q
			14.2	20.0	1.0	23.0			CLK	
Setup time	t _{su}	8.0	—	—	9.0		ns		D	
		7.0	—	—	7.0				PRE or CLR	inactive
Hold time	t _h	0.5	—	_	0.5		ns			
Pulse width	t _w	8.0	_	_	9.0		ns		PRE or CLR	"L"
		8.0	—	—	9.0	—			CLK "H" or "L	"

 $V_{CC}=3.3\pm0.3~V$

ltem	Symbol		T _a = 25°C		$T_a = -40$	to 85°C	Unit	Test	FROM	то
nem	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Maximum clock	f _{max}	80	140	_	70	_	MHz	$C_L = 15 \text{ pF}$		
frequency		50	90		45			$C_L = 50 \text{ pF}$		
Propagation	t _{PLH}	_	6.9	12.3	1.0	14.5	ns	C _L = 15 pF	PRE/CLR	Q or Q
delay time	t _{PHL}	_	7.9	11.9	1.0	14.0			CLK	
		_	9.2	15.8	1.0	18.0		C _L = 50 pF	PRE/CLR	Q or Q
		_	10.2	15.4	1.0	17.5			CLK	
Setup time	t _{su}	6.0			7.0		ns		D	
		5.0			5.0				PRE or CLR	inactive
Hold time	t _h	0.5			0.5		ns			
Pulse width	t _w	6.0			7.0		ns		PRE or CLR	"L"
		6.0			7.0				CLK "H" or "l	"

 $V_{CC}=5.0\pm0.5~V$

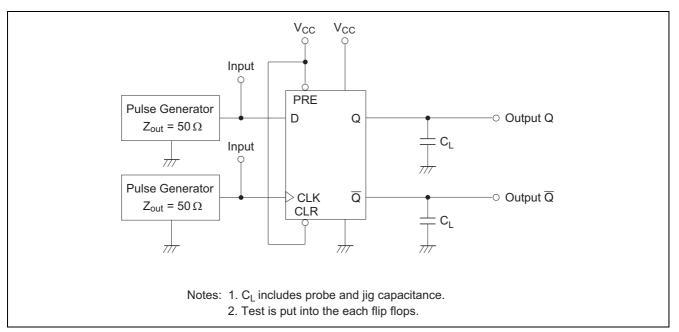
ltom	Symbol		T _a = 25°C		$T_a = -40$	to 85°C	l lmit	Test	FROM	ТО
Item	Symbol	Min	Тур	Max	Min	Max	Unit	Conditions	(Input)	(Output)
Maximum clock	f _{max}	130	180	—	110	_	MHz	C _L = 15 pF		
frequency		90	140	—	75	_		C _L = 50 pF		
Propagation	t _{PLH}	_	5.0	7.7	1.0	9.0	ns	C _L = 15 pF	PRE/CLR	Q or Q
delay time	t _{PHL}		5.6	7.3	1.0	8.5			CLK	
			6.6	9.7	1.0	11.0		C _L = 50 pF	PRE/CLR	Q or Q
			7.2	9.3	1.0	10.5			CLK	
Setup time	t _{su}	5.0	—	—	5.0	_	ns		D	
		3.0	—	—	3.0	_			PRE or CLR	inactive
Hold time	t _h	0.5	_	—	0.5		ns			
Pulse width	t _w	5.0	_	_	5.0		ns		PRE or CLR	"L"
		5.0	—	—	5.0	—			CLK "H" or "I	"

Operating Characteristics

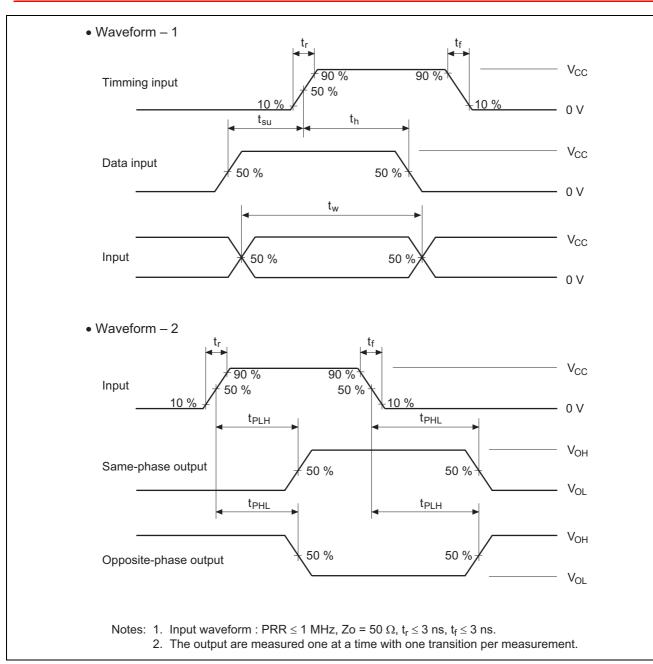
 $C_L = 50 \ pF$

ltem	Symbol	V _{cc} (V)		T _a = 25°C		Unit	Test Conditions	
item	Symbol		Min	Тур	Max	Unit	Test Conditions	
Power dissipation	CPD	3.3	—	13.0	_	pF	f = 10 MHz	
capacitance		5.0	—	14.0	_			

Test Circuit









Package Dimensions

JEITA Package Code	RENESAS Code Previous Code MASS[Typ.]		
P-VSSOP8-2.3x2-0.50	PVSP0008KA-A TTP-8DB/TTP-8DBV 0.010g		
		Terminal cross section $\mathbf{I} = \mathbf{I} + \mathbf{I} +$	Reference Symbol Dimension in Millimeters Min Nom Max D 1.8 2.0 2.2 E 2.2 2.3 2.4 A2 0.6 0.7 0.8 A1 0 0.1 A bp 0.15 0.22 0.3 b1 0.1 C 0.08 0.13 0.23 C1 HE 2.8 3.1 3.4 (E) (0.5) X Y Q HE 2.8 3.1 3.4 (E) (0.5) X Q Y



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Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jalan Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510

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